

# ZX5T2E6

---

## 20V PNP LOW SAT MEDIUM POWER TRANSISTOR IN SOT23-6

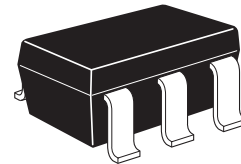
---

### SUMMARY

$BV_{CEO} = -20V$  ;  $R_{SAT} = 31m\Omega$  ;  $I_C = -3.5A$

### DESCRIPTION

Packaged in the SOT23-6 outline this new 5<sup>th</sup> generation low saturation 20V PNP transistor offers extremely low on state losses making it ideal for use in DC-DC circuits and various driving and power management functions.



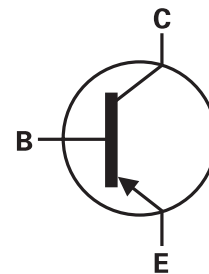
SOT23-6

### FEATURES

- 3.5 Amps continuous current
- Extremely low saturation voltage (-70mV max @ 1A/100mA )
- Up to 10 Amps peak current
- Very low saturation voltages

### APPLICATIONS

- DC - DC converters
- Battery charging
- Power switches
- Motor control
- Power management functions



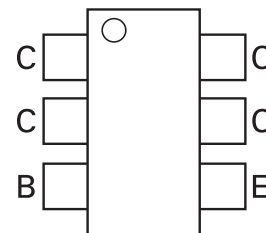
### ORDERING INFORMATION

DEVICE	REEL SIZE	TAPE WIDTH	QUANTITY PER REEL
ZX5T2E6TA	7"	8mm embossed	3,000
ZX5T2E6TC	13"	8mm embossed	10,000

### DEVICE MARKING

- 52

### PINOUT



TOP VIEW

# ZX5T2E6

## ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	LIMIT	UNIT
Collector-base voltage	$BV_{CBO}$	-25	V
Collector-emitter voltage	$BV_{CEO}$	-20	V
Emitter-base voltage	$BV_{EBO}$	-7.5	V
Continuous collector current	$I_C$	-3.5	A
Peak pulse current	$I_{CM}$	-10	A
Power dissipation at $T_A = 25^\circ\text{C}$ <sup>(a)</sup>	$P_D$	1.1	W
Linear derating factor		8.8	mW/ $^\circ\text{C}$
Power dissipation at $T_A = 25^\circ\text{C}$ <sup>(b)</sup>	$P_D$	1.7	W
Linear derating factor		13.6	mW/ $^\circ\text{C}$
Operating and storage temperature range	$T_j, T_{stg}$	-55 to + 150	$^\circ\text{C}$

## THERMAL RESISTANCE

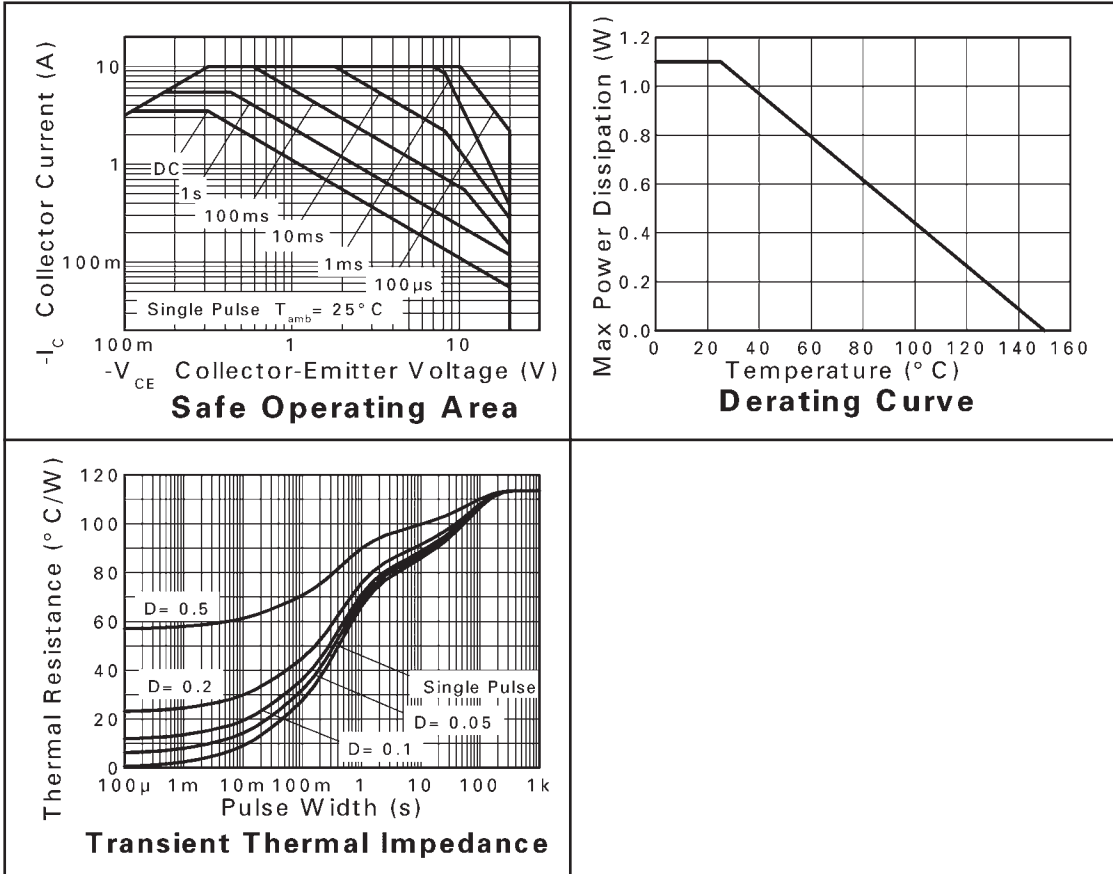
PARAMETER	SYMBOL	VALUE	UNIT
Junction to ambient <sup>(a)</sup>	$R_{\theta JA}$	113	$^\circ\text{C}/\text{W}$
Junction to ambient <sup>(b)</sup>	$R_{\theta JC}$	73	$^\circ\text{C}/\text{W}$

### NOTES

- (a) For a device surface mounted on 25mm x 25mm x 0.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.  
(b) As above measured at  $t < 5$  seconds.

# ZX5T2E6

## CHARACTERISTICS



# ZX5T2E6

## ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ unless otherwise stated)

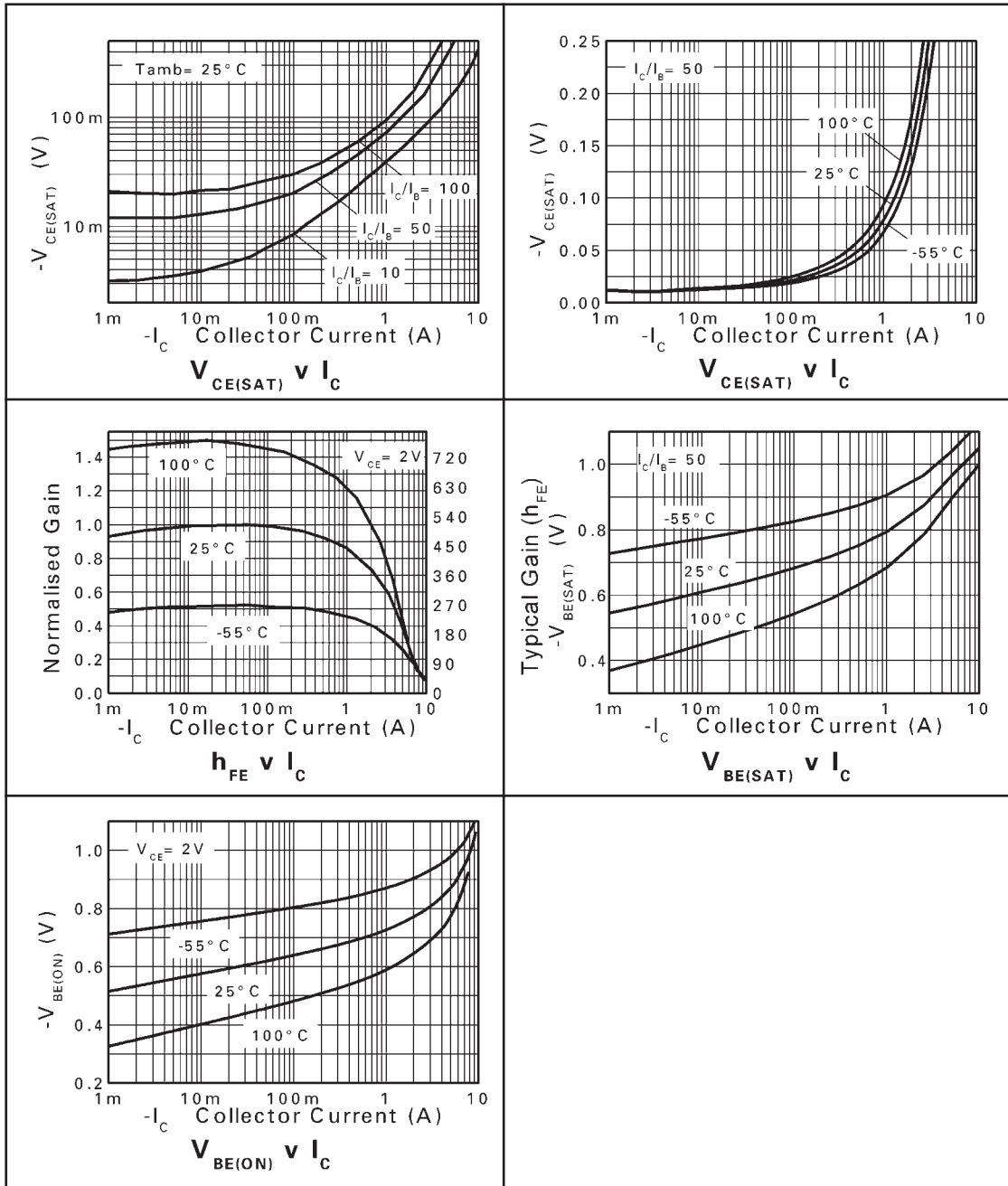
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS
Collector-base breakdown voltage	$BV_{CBO}$	-25	-49		V	$I_C = -100\mu A$
Collector-emitter breakdown voltage	$BV_{CEO}$	-20	-43		V	$I_C = -10mA$ *
Emitter-base breakdown voltage	$BV_{EBO}$	-7.5	-8.4		V	$I_E = -100\mu A$
Collector cut-off current	$I_{CBO}$			-100	nA	$V_{CB} = -20V$
Collector cut-off current	$I_{CES}$			-100	nA	$V_{CB} = -20V$
Emitter cut-off current	$I_{EBO}$			-100	nA	$V_{EB} = -6V$
Collector-emitter saturation voltage	$V_{CE(SAT)}$		-10	-15	mV	$I_C = -0.1A, I_B = -10mA$ *
			-100	-140	mV	$I_C = -1A, I_B = -10mA$ *
			-110	-130	mV	$I_C = -3.5A, I_B = -350mA$ *
Base-emitter saturation voltage	$V_{BE(SAT)}$		-0.96	-1.1	V	$I_C = -3.5A, I_B = -350mA$ *
Base-emitter turn-on voltage	$V_{BE(ON)}$		-0.8	-0.9	V	$I_C = -3.5A, V_{CE} = -2V$ *
Static forward current transfer ratio	$h_{FE}$	300	575			$I_C = -10mA, V_{CE} = -2V$ *
		300	450	900		$I_C = -1A, V_{CE} = -2V$ *
		150	285			$I_C = -3.5A, V_{CE} = -2V$ *
		10	40			$I_C = -10A, V_{CE} = -2V$ *
Transition frequency	$f_T$		110			$I_C = -50mA, V_{CE} = -10V$ $f = 50MHz$
Output capacitance	$C_{OBO}$		45		pF	$V_{CB} = -10V, f = 1MHz$ *
Switching times	$t_{ON}$		90		ns	$I_C = -2A, V_{CC} = -10V,$
	$t_{OFF}$		325		ns	$I_{B1} = I_{B2} = -40mA$

### NOTES

\* Measured under pulsed conditions. Pulse width  $\leq 300\mu s$ ; duty cycle  $\leq 2\%$ .

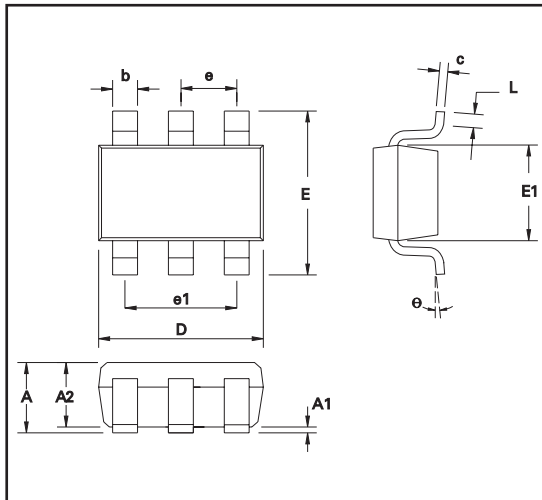
# ZX5T2E6

## TYPICAL CHARACTERISTICS

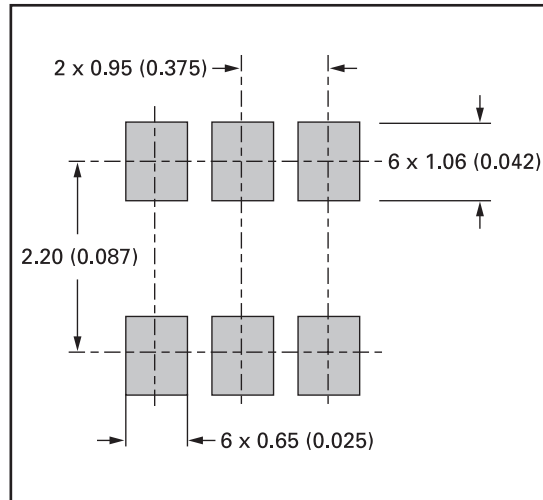


# ZX5T2E6

## PACKAGE OUTLINE



## PAD LAYOUT DETAILS



Controlling dimensions are in millimeters. Approximate conversions are given in inches

## PACKAGE DIMENSIONS

DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min	Max	Min	Max		Min	Max	Min	Max
A	0.90	1.45	0.035	0.057	E	2.20	3.20	0.0866	0.118
A1	0.00	0.15	0.00	0.006	E1	1.30	1.80	0.0511	0.071
A2	0.90	1.30	0.035	0.051	L	0.10	0.60	0.004	0.024
b	0.20	0.50	0.008	0.020	e	0.95 REF		0.037 REF	
C	0.09	0.26	0.003	0.010	e1	1.90 REF		0.075 REF	
D	2.70	3.10	0.106	0.122	θ	0°	30°	0°	30°

©Zetex Semiconductors plc 2004

Europe	Americas	Asia Pacific	Corporate Headquarters
Zetex GmbH Streitfeldstraße 19 D-81673 München Germany	Zetex Inc 700 Veterans Memorial Hwy Hauppauge, NY 11788 USA	Zetex (Asia) Ltd 3701-04 Metroplaza Tower 1 Hing Fong Road, Kwai Fong Hong Kong	Zetex Semiconductors plc Zetex Technology Park, Chadderton Oldham, OL9 9LL United Kingdom
Telefon: (49) 89 45 49 49 0 Fax: (49) 89 45 49 49 49 europe.sales@zetex.com	Telephone: (1) 631 360 2222 Fax: (1) 631 360 8222 usa.sales@zetex.com	Telephone: (852) 26100 611 Fax: (852) 24250 494 asia.sales@zetex.com	Telephone: (44) 161 622 4444 Fax: (44) 161 622 4446 hq@zetex.com

These offices are supported by agents and distributors in major countries world-wide.

This publication is issued to provide outline information only which (unless agreed by the Company in writing) may not be used, applied or reproduced for any purpose or form part of any order or contract or be regarded as a representation relating to the products or services concerned. The Company reserves the right to alter without notice the specification, design, price or conditions of supply of any product or service.

For the latest product information, log on to [www.zetex.com](http://www.zetex.com)



ISSUE 1 - MAY 2004